High Voltage Transistors
NPN Silicon

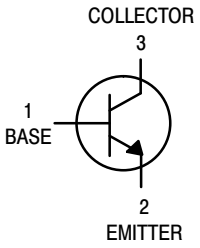
MMBT5550L, MMBT5551L

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

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MAXIMUM RATINGS

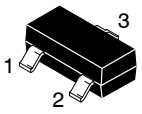
Rating	Symbol	Value	Unit
Collector − Emitter Voltage MMBT5550 MMBT5551	V_{CEO}	 140 160	Vdc
Collector − Base Voltage MMBT5550 MMBT5551	V_{CBO}	 160 180	Vdc
Emitter − Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc
Electrostatic Discharge Human Body Model Machine Model	ESD	 > 8000 > 400	V

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR− 5 Board (Note 1) @T_A = 25°C Derate Above 25°C	P_D	 225 1.8	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T_A = 25°C Derate Above 25°C	P_D	 300 2.4	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

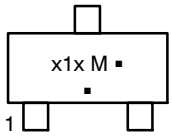
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR− 5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.



SOT−23 (TO−236)
CASE 318
STYLE 6

MARKING DIAGRAM



x1x = Device Code
M1F = MMBT5550LT
G1 = MMBT5551LT
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5550LT1G, NSVMMBT5550LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBT5550LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
MMBT5551LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBT5551LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
SMMBT5551LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3)		$V_{(BR)CEO}$			Vdc
(I_C = 1.0 mAdc, I_B = 0)	MMBT5550		140	–	
	MMBT5551		160	–	
Collector – Base Breakdown Voltage		$V_{(BR)CBO}$			Vdc
(I_C = 100 μAdc, I_E = 0)	MMBT5550		160	–	
	MMBT5551		180	–	
Emitter – Base Breakdown Voltage		$V_{(BR)EBO}$			Vdc
(I_E = 10 μAdc, I_C = 0)			6.0	–	
Collector Cutoff Current		I_{CBO}			
(V_{CB} = 100 Vdc, I_E = 0)	MMBT5550		–	100	nAdc
(V_{CB} = 120 Vdc, I_E = 0)	MMBT5551		–	50	
(V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C)	MMBT5550		–	100	μAdc
(V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	MMBT5551		–	50	
Emitter Cutoff Current		I_{EBO}			nAdc
(V_{EB} = 4.0 Vdc, I_C = 0)			–	50	
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			–
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550		60	–	
	MMBT5551		80	–	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550		60	250	
	MMBT5551		80	250	
(I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550		20	–	
	MMBT5551		30	–	
Collector – Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types		–	0.15	
(I_C = 50 mAdc, I_B = 5.0 mAdc)	MMBT5550		–	0.25	
	MMBT5551		–	0.20	
Base – Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types		–	1.0	
(I_C = 50 mAdc, I_B = 5.0 mAdc)	MMBT5550		–	1.2	
	MMBT5551		–	1.0	
Collector Emitter Cut–off		I_{CES}			nA
(V_{CB} = 10 V)	Both Types		–	50	
(V_{CB} = 75 V)			–	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

TYPICAL CHARACTERISTICS

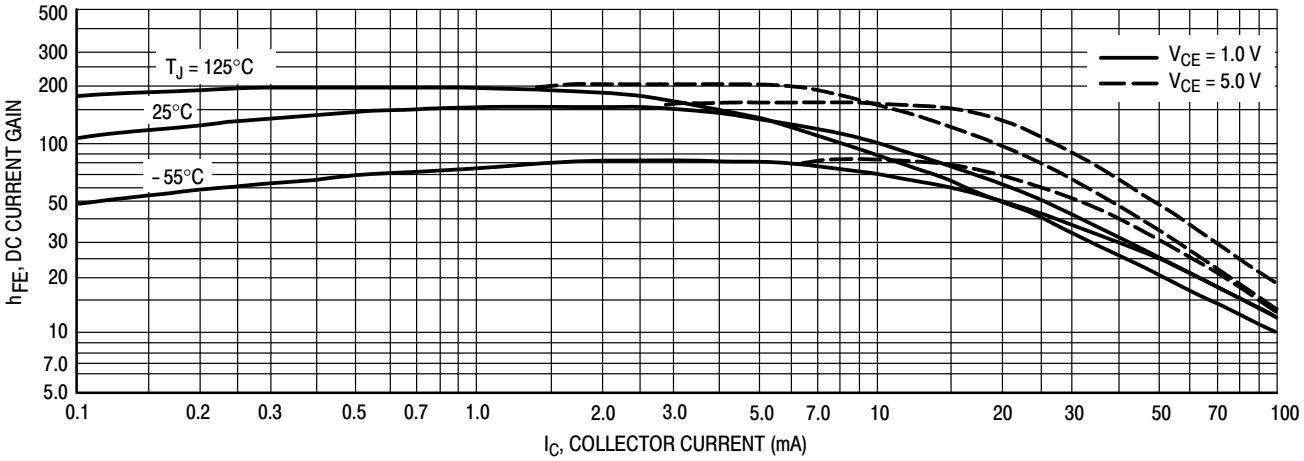


Figure 1. DC Current Gain

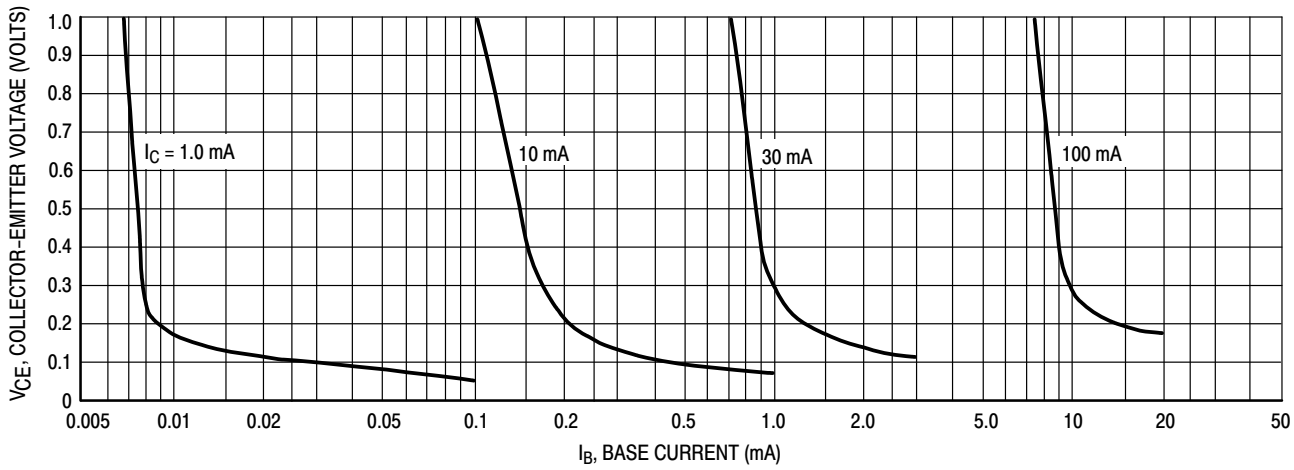


Figure 2. Collector Saturation Region

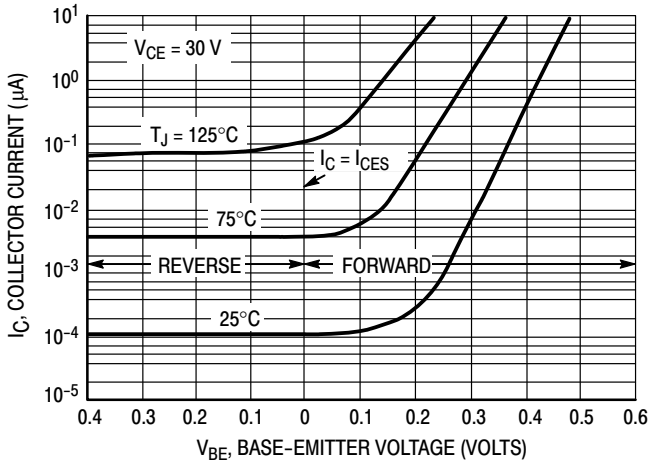


Figure 3. Collector Cut−Off Region

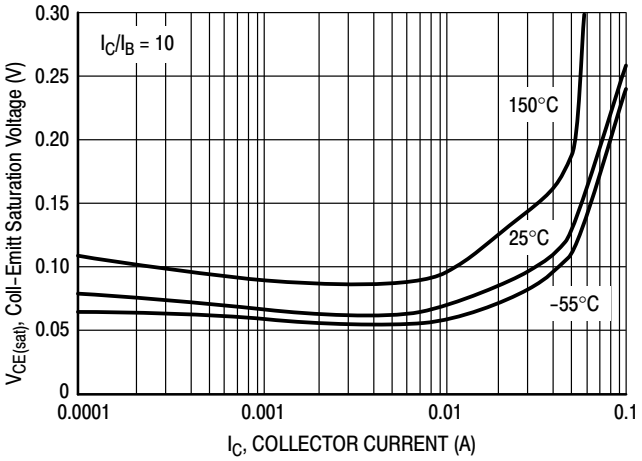


Figure 4. $V_{CE(sat)}$

TYPICAL CHARACTERISTICS

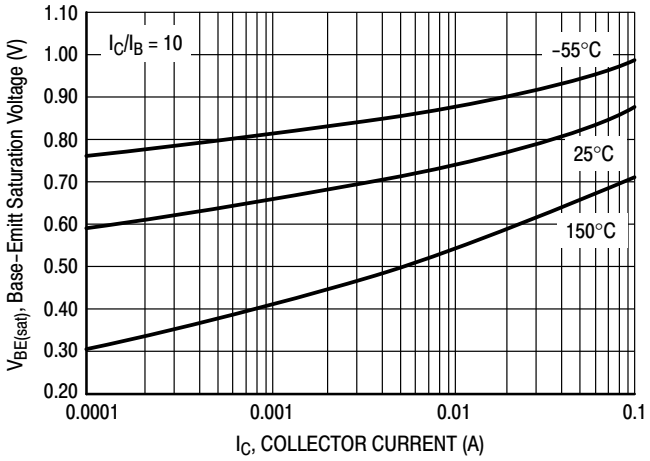


Figure 5. $V_{BE(sat)}$

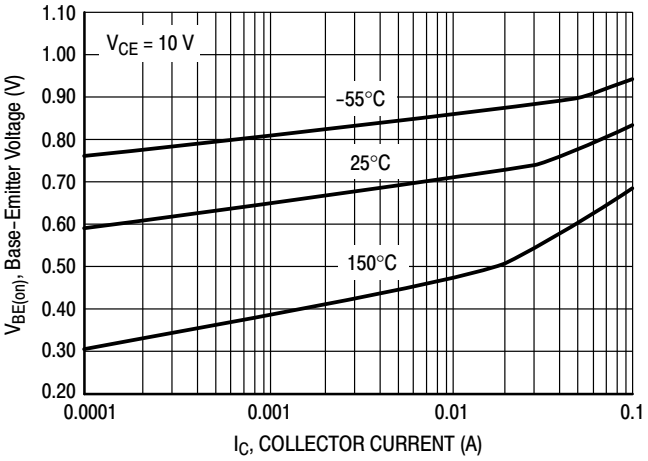


Figure 6. $V_{BE(on)}$

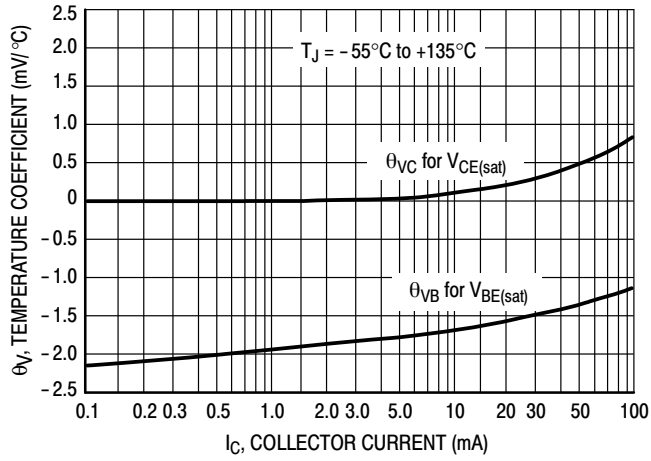


Figure 7. Temperature Coefficients

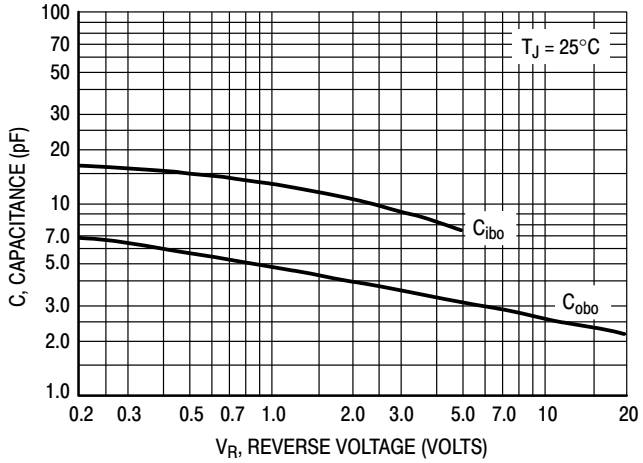
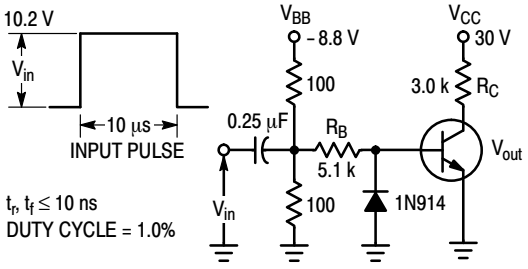


Figure 8. Capacitances



Values Shown are for I_C @ 10 mA

Figure 9. Switching Time Test Circuit

TYPICAL CHARACTERISTICS

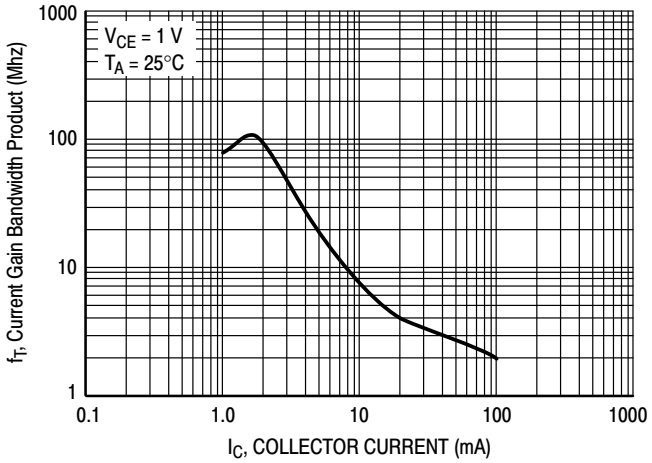


Figure 10. Current Gain Bandwidth Product

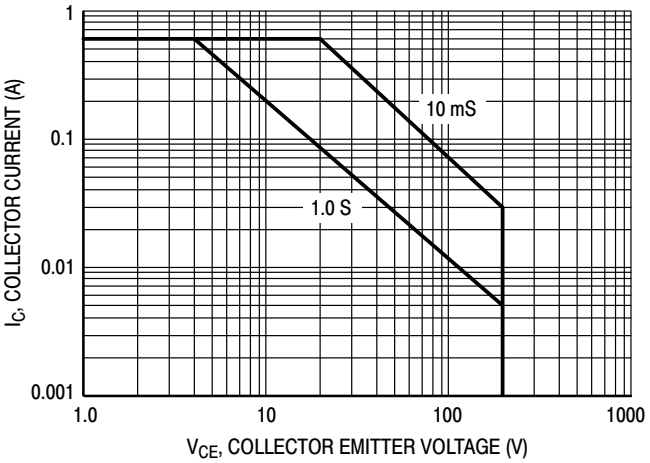


Figure 11. Safe Operating Area

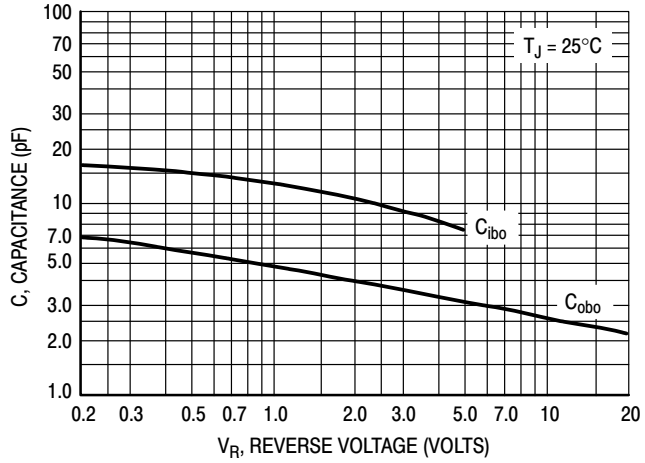


Figure 12. Capacitances

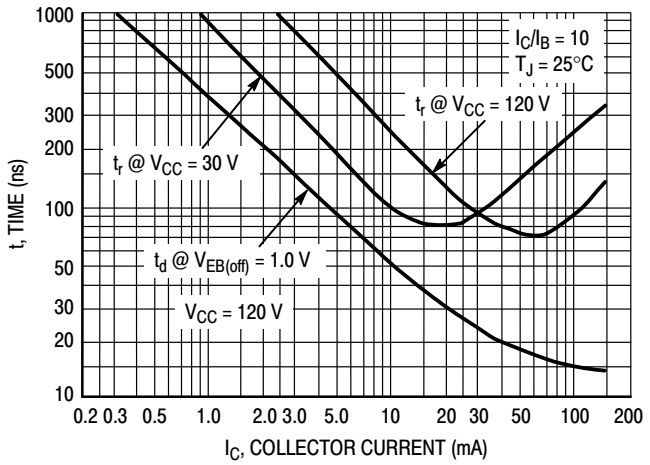
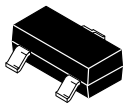


Figure 13. Turn−On Time

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

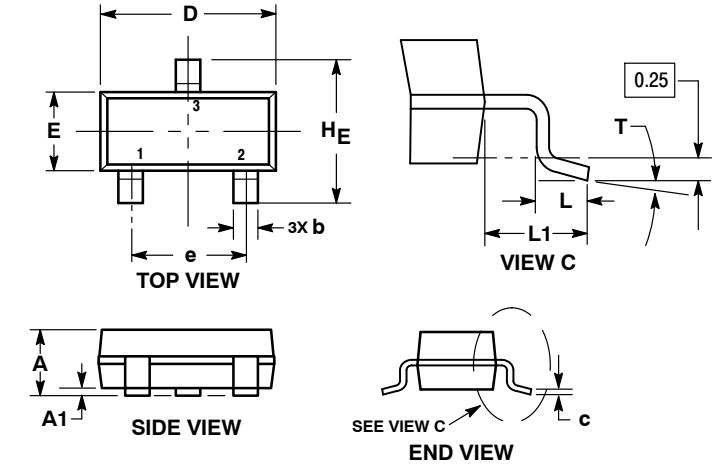
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SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

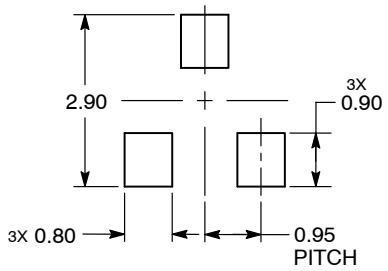
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

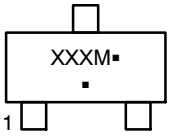
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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DESCRIPTION:	SOT−23 (TO−236)	PAGE 1 OF 1

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